## 1. General description

PNP high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

NPN complement: MJD31CA

### 2. Features and benefits

- · High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- · Electrically similar to popular MJD32 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- AEC-Q101 qualified

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- Relay replacement

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-5	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -4 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	25	-	-	
		V <sub>CE</sub> = -4 V; I <sub>C</sub> = -3 A; T <sub>amb</sub> = 25 °C	10	-	50	



100 V, 3 A PNP high power bipolar transistor

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	E
2	С	collector		в -{м
3	Е	emitter		C; mb
mb	С	mounting base; connected to collector	DPAK (SOT428C)	aaa-029523

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
MJD32CA	DPAK	Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

## 7. Marking

### Table 4. Marking codes

Type number	Marking code
MJD32CA	MJD32CA

# 8. Limiting values

### Table 5. Limiting values

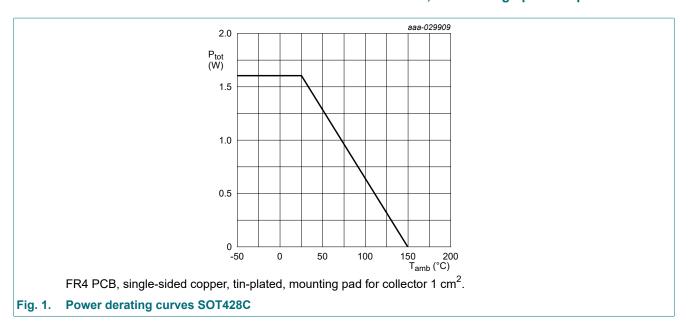
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-100	V
$V_{EBO}$	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	[1]	-	15	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Total power dissipation junction to mounting base.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

### 100 V, 3 A PNP high power bipolar transistor

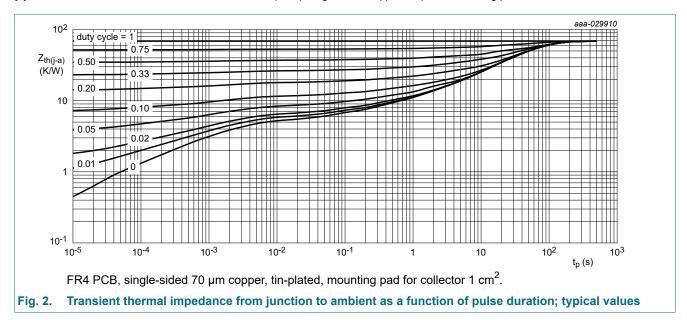


### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	in free air		-	-	9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1]	-	-	79	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.



### 100 V, 3 A PNP high power bipolar transistor

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CES</sub>	collector-emitter cut-off	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-1	μΑ
	current	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-1	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -4 V; I <sub>C</sub> = -1 A; T <sub>amb</sub> = 25 °C	25	-	-	
		V <sub>CE</sub> = -4 V; I <sub>C</sub> = -3 A; T <sub>amb</sub> = 25 °C	10	-	50	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -3 \text{ A}; I_B = -375 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-1.2	V
$V_{BE}$	base-emitter voltage	$V_{CE}$ = -4 V; $I_{C}$ = -3 mA; $T_{amb}$ = 25 °C	-	-	-1.8	mV
h <sub>fe</sub>	small-signal current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -500 A; f = 1 kHz; T <sub>amb</sub> = 25 °C	20	-	-	
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	3	-	-	MHz

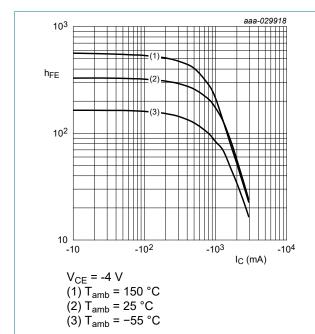


Fig. 3. DC current gain as a function of collector current; typical values

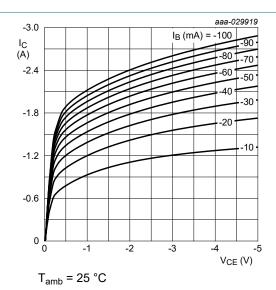
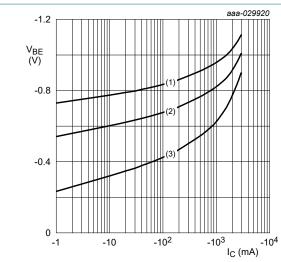


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

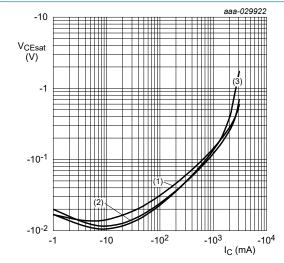
### 100 V, 3 A PNP high power bipolar transistor



$$V_{CF} = -5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



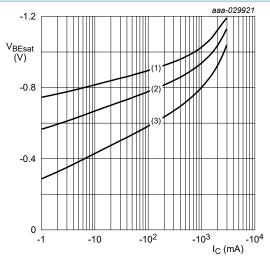
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

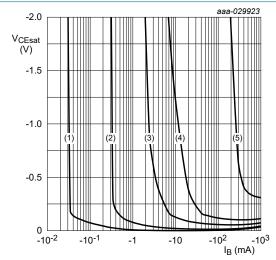


$$I_{\rm C}/I_{\rm B} = 10$$

$$I_{\rm C}/I_{\rm B} = 10$$
  
(1)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$   
(2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$   
(3)  $T_{\rm amb} = 150~{\rm ^{\circ}C}$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



(1)  $I_C = -10 \text{ mA}$ 

(2)  $I_C = -100 \text{ mA}$ 

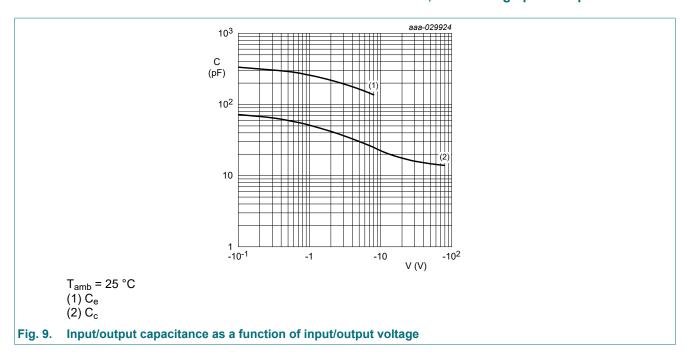
(3)  $I_C = -500 \text{ mA}$ 

 $(4) I_C = -1000 \text{ mA}$ 

 $(5) I_C = -3000 \text{ mA}$ 

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

### 100 V, 3 A PNP high power bipolar transistor



# 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 100 V, 3 A PNP high power bipolar transistor

# 12. Package outline

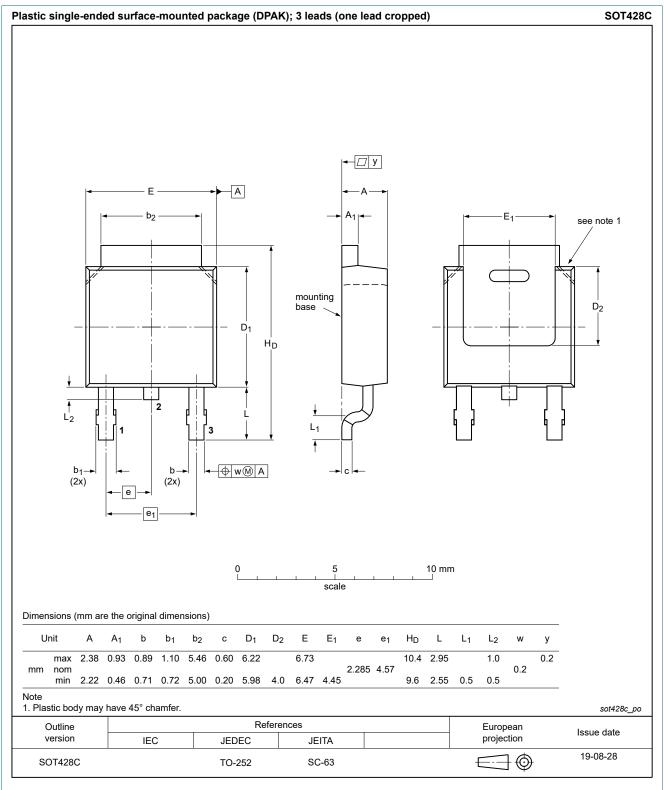
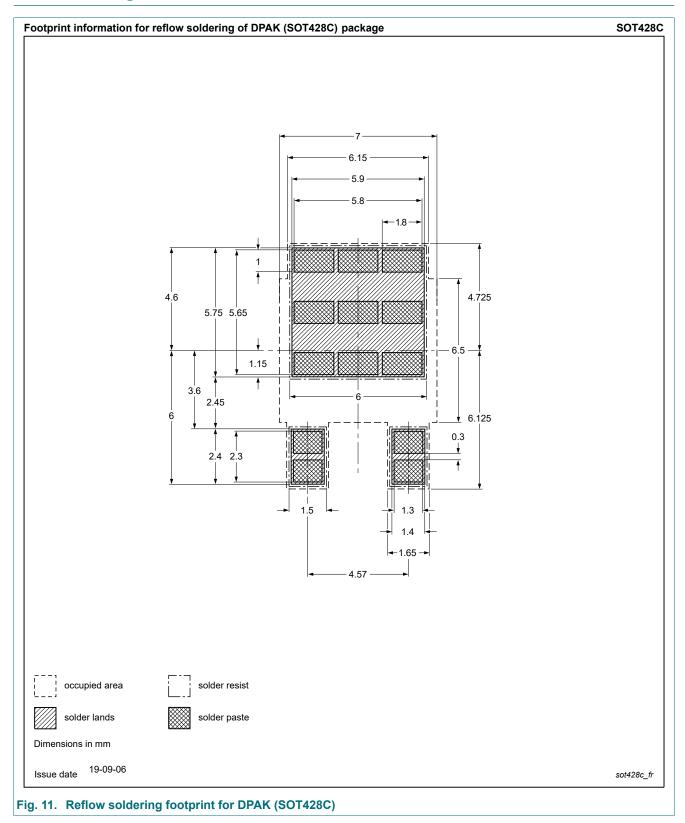


Fig. 10. Package outline DPAK (SOT428C)

100 V, 3 A PNP high power bipolar transistor

# 13. Soldering



8 / 11

### 100 V, 3 A PNP high power bipolar transistor

# 14. Revision history

### **Table 8. Revision history**

Table 6. Itevision i	iistoi y			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
MJD32CA v.6	20201123	Product data sheet	-	MJD32CA v.5
Modifications:	Characteristics	h <sub>fe</sub> : conditions corrected		
MJD32CA v.5	20190930	Product data sheet	-	MJD32CA v.4
MJD32CA v.4	20190912	Product data sheet	-	MJD32CA v.3
MJD32CA v.3	20190802	Product data sheet	-	MJD32CA v.2
MJD32CA v.2	20190729	Product data sheet	-	MJD32CA v.1
MJD32CA v.1	20190523	Preliminary data sheet	: <b>-</b>	-

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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### 100 V, 3 A PNP high power bipolar transistor

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
	Thermal characteristics	
10.	. Characteristics	4
	Test information	
	. Package outline	
	. Soldering	
	Revision history	
	. Legal information	

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